

This Sheet Has Been Replaced



SIC SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

A semiconductor device structure having an epitaxial layer, formed of silicon for example, is disposed on a high band-gap material, such as silicon carbide, which is in turn disposed on a semiconductor substrate, such as silicon. The high band gap material achieves a charge concentration much higher than that of a conventional semiconductor material for the same breakdown voltage.

Figure 1.